



Metal Oxide Semiconductors for Electronic Applications

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Message from the Guest Editors

Dear Colleagues,

New era concepts of Internet of things (IoT) and smart surfaces are now demanding transparent, flexible, and nanoscale devices and materials. In this regard, metal oxides have emerged as key materials, since they present good reproducibility, large-area uniformity, and lower fabrication temperatures and costs.

This Special Issue aims to collect original papers and/or review articles focused on the fabrication of metal oxide semiconductors, in both the form of thin films or nanostructures, and their application in electronics.

Relevant topics may include (but are not limited to):

- Metal oxide semiconductors characterization and fabrication;
- Sustainable materials and processes;
- Advances in the integration of metal oxide semiconductor nanostructures;
- Transparent and flexible electronics;
- Electronic devices such as field effect transistors, memristors, sensors, nanogenerators, and photodetectors;
- Application of metal oxide semiconductors to electronic circuits or systems;
- Devices' modelling and simulation.